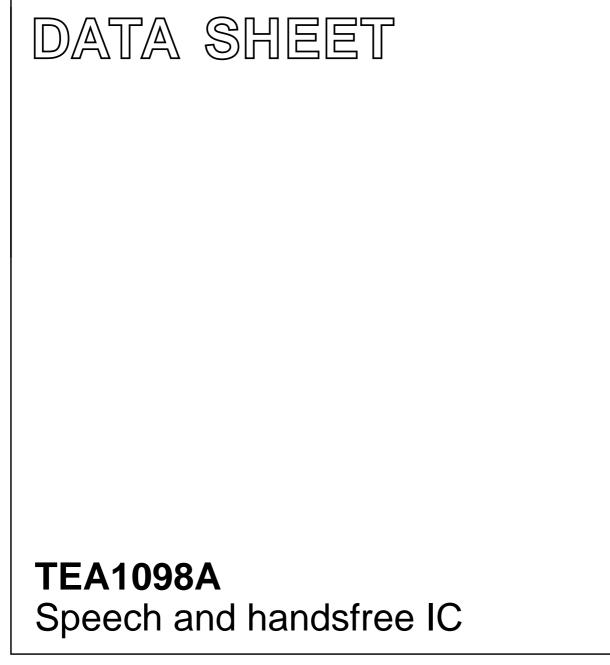
# INTEGRATED CIRCUITS



Product specification Supersedes data of 2000 Jun 08 File under Integrated Circuits, IC03 2000 Aug 18



## **TEA1098A**

#### FEATURES

#### Line interface

- · Low DC line voltage
- · Voltage regulator with adjustable DC voltage
- Symmetrical high impedance inputs (70 kΩ) for dynamic, magnetic or electret microphones
- DTMF input with confidence tone on earphone and/or loudspeaker
- Earphone amplifier for dynamic, magnetic or piezo-electric earpieces (with externally adjustable gain)
- Digital volume control on earphone amplifier (4 steps)
- Automatic Gain Control (AGC) for true line loss compensation
- Microphone mute
- Key tone mode.

#### Supplies

- Provides a strong 3.35 V regulated supply for microcontroller or dialler
- Provides filtered power supply, optimized according to line current
- Filtered 2.0 V power supply output for electret microphone
- PD logic input for power-down.

#### Handsfree

- Asymmetrical high input impedance for electret microphone
- Loudspeaker amplifier with single-ended rail-to-rail output and externally adjustable gain

#### ORDERING INFORMATION

- Dynamic limiter on loudspeaker amplifier to prevent distortion
- Digital volume control on loudspeaker amplifier (8 steps)
- Duplex controller consisting of:
  - Signal and noise envelope monitors for both channels (with adjustable sensitivities and timing)
  - Decision logic (with adjustable switch-over and Idle mode timing)
  - Voice switch control (with adjustable switching range and constant sum of gain during switching).

#### **APPLICATIONS**

• Line powered telephone sets.

#### **GENERAL DESCRIPTION**

The TEA1098A is an analog bipolar circuit dedicated for telephony applications. It includes a line interface, handset (HS) microphone and earpiece amplifiers, handsfree (HF) microphone and loudspeaker amplifiers and a duplex controller with signal and noise monitors on both channels. Digital volume control is available both on earphone and loudspeaker amplifiers.

This IC provides a 3.35 V strong supply for a microcontroller and a 2.0 V filtered voltage supply for an electret microphone.

TYPE NUMBER		PACKAGE				
ITPE NOMBER	NAME	DESCRIPTION	VERSION			
TEA1098ATV	VSO40	plastic very small outline package; 40 leads	SOT158-1			
TEA1098AUH	_	bare die; on foil	_			

#### TEA1098A

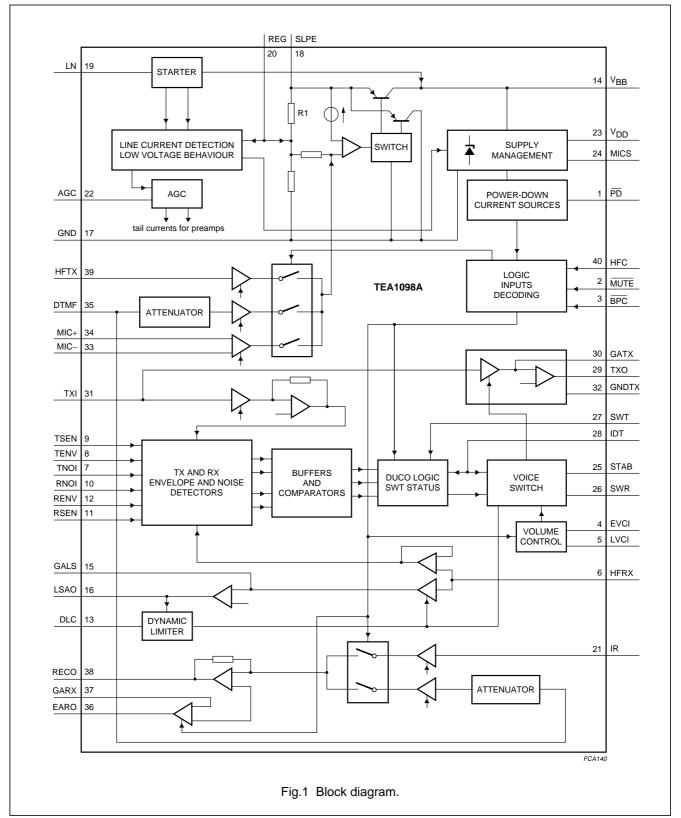
#### QUICK REFERENCE DATA

 $I_{line} = 15 \text{ mA}$ ;  $R_{SLPE} = 20 \Omega$ ;  $Z_{line} = 600 \Omega$ ; f = 1 kHz;  $T_{amb} = 25 \text{ °C}$  for TEA1098ATV;  $T_j = 25 \text{ °C}$  for TEA1098AUH; AGC pin connected to LN;  $\overline{PD} = HIGH$ ; HFC = LOW;  $\overline{MUTE} = HIGH$ ;  $\overline{BPC} = HIGH$ ; measured according to test circuits; unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I <sub>line</sub>	line current operating	normal operation	11	_	130	mA
	range	with reduced performance	1	_	11	mA
V <sub>SLPE</sub>	stabilized voltage between	I <sub>line</sub> = 15 mA	3.4	3.7	4.0	V
	SLPE and GND	I <sub>line</sub> = 70 mA	5.7	6.1	6.5	V
V <sub>BB</sub>	regulated supply voltage	I <sub>line</sub> = 15 mA	2.75	3.0	3.25	V
	for internal circuitry	I <sub>line</sub> = 70 mA	4.9	5.3	5.7	V
V <sub>DD</sub>	regulated supply voltage on pin $V_{DD}$	V <sub>BB</sub> > 3.35 V + 0.25 V (typ.)	3.1	3.35	3.6	V
		otherwise	_	V <sub>BB</sub> - 0.25	-	V
I <sub>BB</sub>	current available on pin $V_{BB}$					
	in speech mode		-	11	-	mA
	in handsfree mode		-	9	-	mA
I <sub>BB(PD)</sub>	current consumption on pin $V_{BB}$ during power-down phase	PD = LOW	_	460	-	μA
G <sub>v(MIC-LN)</sub>	voltage gain from pin MIC+/MIC– to LN	V <sub>MIC</sub> = 5 mV (RMS)	43.3	44.3	45.3	dB
G <sub>v(IR-RECO)</sub>	voltage gain from pin IR (referenced to LN) to RECO	V <sub>IR</sub> = 15 mV (RMS); HFC = HIGH	28.7	29.7	30.7	dB
$\Delta G_{v(RECO-EARO)}$	gain voltage range between pins RECO and EARO		-3	-	+15	dB
G <sub>v(TXI-TXO)</sub>	voltage gain from pin TXI to TXO	$V_{TXI} = 3 \text{ mV} (RMS);$ $R_{GATX} = 30.1 \text{ k}\Omega$	12.7	15.2	17.7	dB
G <sub>v(HFTX-LN)</sub>	voltage gain from pin HFTX to LN	V <sub>HFTX</sub> = 15 mV (RMS)	33.5	34.7	35.9	dB
G <sub>v(HFRX-LSAO</sub> )	voltage gain from pin HFRX to LSAO	$\label{eq:HFRX} \begin{array}{l} V_{HFRX} = 30 \text{ mV (RMS)};\\ R_{GALS} = 255 \text{ k}\Omega;\\ I_{line} = 70 \text{ mA} \end{array}$	25.5	28	30.5	dB
SWR	switching range		_	40	-	dB
∆SWR	switching range adjustment	with $R_{SWR}$ referenced to 365 k $\Omega$	-40	-	+12	dB
$\Delta G_{v(trx)}$	gain control range for transmit and receive amplifiers affected by the AGC; with respect to $I_{line} = 15 \text{ mA}$	I <sub>line</sub> = 70 mA	5.45	6.45	7.45	dB

# TEA1098A

#### **BLOCK DIAGRAM**



# TEA1098A

#### PINNING

	PIN	PAD	DECODIDION
SYMBOL	TEA1098ATV	TEA1098AUH	DESCRIPTION
PD	1	40	power-down input (active LOW)
MUTE	2	41	logic input (active LOW)
BPC	3	42	logic input (active LOW)
EVCI	4	43	logic input for digital volume control (earpiece and loudspeaker LSB)
LVCI	5	44	logic input for digital volume control (loudspeaker MSB)
HFRX	6	1	receive input for loudspeaker amplifier
TNOI	7	2	transmit noise envelope timing adjustment
TENV	8	3	transmit signal envelope timing adjustment
TSEN	9	4	transmit signal envelope sensitivity adjustment
RNOI	10	5	receive noise envelope timing adjustment
RSEN	11	6	receive signal envelope sensitivity adjustment
RENV	12	7	receive signal envelope timing adjustment
DLC	13	8	dynamic limiter capacitor for the loudspeaker amplifier
V <sub>BB</sub>	14	9	stabilized supply for internal circuitry
GALS	15	10	loudspeaker amplifier gain adjustment
LSAO	16	11	loudspeaker amplifier output
n.c.	_	12	not connected
GND	17	13	ground reference
SLPE	18	14 and 15	line current sense
LN	19	16	positive line terminal
REG	20	17	line voltage regulator decoupling
IR	21	18	receive amplifier input
AGC	22	19	automatic gain control/line loss compensation
V <sub>DD</sub>	23	20	3.35 V regulated voltage supply for microcontrollers
MICS	24	21	microphone supply
STAB	25	22	reference current adjustment
SWR	26	23	switching range adjustment
n.c.	_	24	not connected
SWT	27	25	switch-over timing adjustment
IDT	28	26	Idle mode timing adjustment
ТХО	29	27	handsfree microphone amplifier output
GATX	30	28	handsfree microphone amplifier gain adjustment
TXI	31	29	handsfree microphone amplifier input
GNDTX	32	30 and 31	ground reference for microphone amplifiers
MIC-	33	32	negative handset microphone amplifier input
MIC+	34	33	positive handset microphone amplifier input
DTMF	35	34	dual tone multi-frequency input
EARO	36	35	earpiece amplifier output

SYMBOL	PIN	PAD	DESCRIPTION	
TEA1098ATV TEA1098AUH		TEA1098AUH		
GARX	37	36	earpiece amplifier gain adjustment	
RECO	38	37	receive amplifier output	
HFTX	39	38	transmit input for line amplifier	
HFC	40	39	logic input	

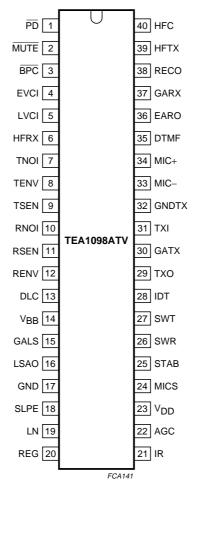


Fig.2 Pin configuration.

# TEA1098A

#### FUNCTIONAL DESCRIPTION

All data given in this chapter are typical values, except when otherwise specified.

#### Supplies

Line interface and internal supply (pins LN, SLPE, REG and  $\mathsf{V}_{\mathsf{BB}})$ 

The supply for the TEA1098A and its peripherals is obtained from the line. The IC generates a stabilized reference voltage ( $V_{ref}$ ) between pins SLPE and GND.

This reference voltage is equal to 3.7 V for line currents lower than 18 mA. It than increases linearly with the line current and reaches the value of 6.1 V for line currents higher than 45 mA. For line currents below 9 mA, the internal reference voltage generating  $V_{ref}$  is automatically adjusted to a lower value. This is the so-called low voltage area and the TEA1098A has limited performances in this area (see Section "Low voltage behaviour"). This reference voltage is temperature compensated.

The voltage between pins SLPE and REG is used by the internal regulator to generate the stabilized reference

voltage and is decoupled by means of a capacitor between pins LN and REG.

This capacitor converted into an equivalent inductance realizes the set impedance conversion from its DC value ( $R_{SLPE}$ ) to its AC value (done by an external impedance).

The IC regulates the line voltage at pin LN and can be calculated as follows:

$$V_{\text{LN}} = V_{\text{ref}} + R_{\text{SLPE}} \times I_{\text{SLPE}}$$

 $I_{SLPE} = I_{line} - I^{x}$ 

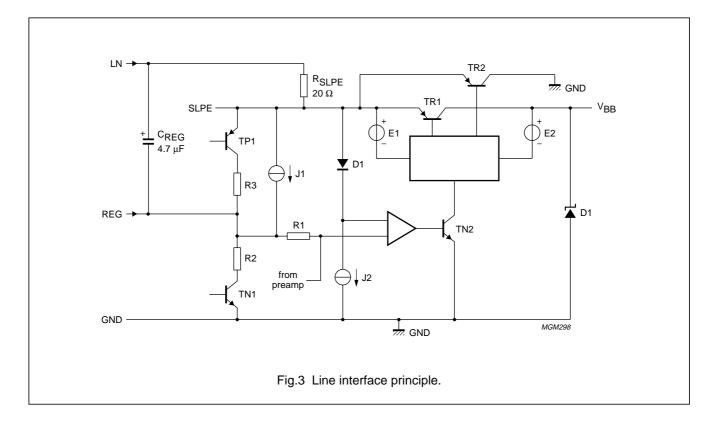
where:

 $I_{line} = line current$ 

 $I^x$  = current consumed on pin LN (approximately a few  $\mu A$ )

 $I_{SLPE}$  = current flowing through the  $R_{SLPE}$  resistor

The preferred value for R<sub>SLPE</sub> is 20  $\Omega$ . Changing this value will affect more than the DC characteristics; it also influences the transmit gains to the line, the gain control characteristic, the sidetone level and the maximum output swing on the line.



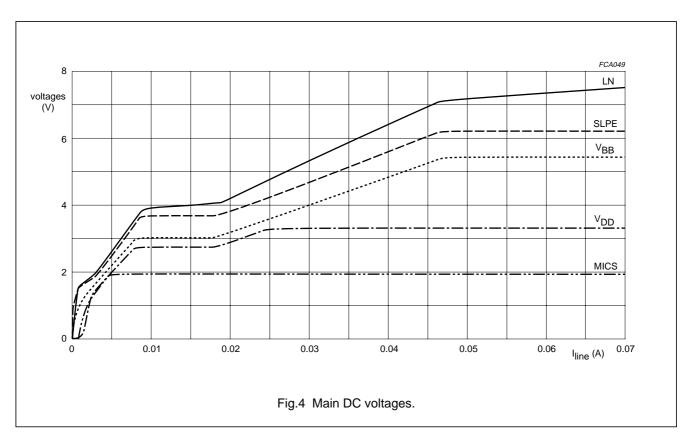
#### TEA1098A

As can be seen from Fig.3, the internal circuitry is supplied by pin  $V_{BB}$ , which is a strong supply point combined with the line interface. The line current is flowing through the  $R_{SLPE}$  resistor and is sunk by the  $V_{BB}$  voltage stabilizer, thus becoming available for a loudspeaker amplifier or any peripheral IC. Its voltage is equal to 3.0 V for line currents lower than 18 mA. It than increases linearly with the line current and reaches the value of 5.3 V for line currents greater than 45 mA. It is temperature compensated.

The aim of the current switch TR1 and TR2 is to reduce distortion of large AC line signals. Current  $I_{SLPE}$  is supplied

to  $V_{BB}$  via TR1 when the voltage on SLPE is greater than  $V_{BB}$  + 0.25 V. When the voltage on SLPE is lower than this value, the current  $I_{SLPE}$  is shunted to GND via TR2.

The reference voltage  $V_{ref}$  can be increased by connecting an external resistor between pins REG and SLPE. For large line currents, this increase can slightly affect some dynamic performances such as maximum signal level on the line for 2% THD. The voltage on pin V<sub>BB</sub> is not affected by this external resistor; see Fig.4 for the main DC voltages.



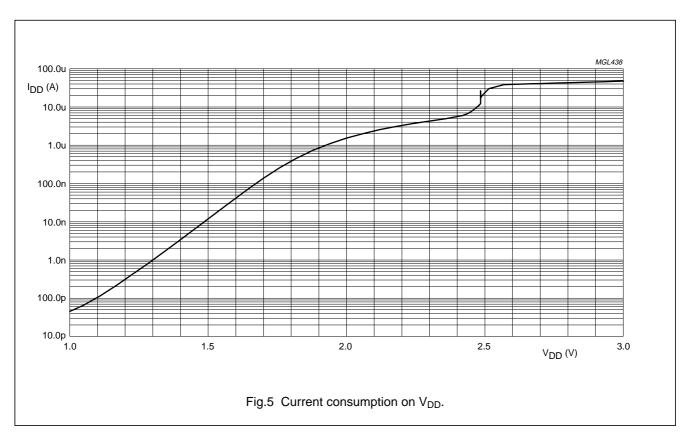
#### $V_{\text{DD}}$ supply for microcontroller (pin $V_{\text{DD}})$

The voltage on the V<sub>DD</sub> supply point follows the voltage on V<sub>BB</sub> with a difference typically equal to 250 mV and is internally limited to 3.35 V. This voltage is temperature compensated. This supply point can provide a current up to 3 mA typically. Its internal consumption stays low (a few 10 nA) as long as V<sub>DD</sub> does not exceed 1.5 V.

 $V_{\text{DD}}$  can also be used as an input; in this case the voltage will be stabilised to 3.35 V up to 75 mA input current.

 $V_{BB}$  and  $V_{DD}$  can supply external circuits in the limit of currents provided from the line, taking into account the internal current consumption.

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#### SUPPLY FOR MICROPHONE (PINS MICS AND GNDTX)

The MICS output can be used as a supply for an electret microphone. Its voltage is equal to 2.0 V; it can source a current up to 1 mA and has an output impedance equal to 200  $\Omega$ .

#### LOW VOLTAGE BEHAVIOUR

For line currents below 9 mA, the reference voltage is automatically adjusted to a lower value; the  $V_{BB}$  voltage follows the SLPE voltage with 250 mV difference. The excess current available for other purposes than DC biasing of the IC becomes small. In this low voltage area, the IC has limited performances.

When the  $V_{BB}$  voltage becomes lower than 2.7 V, the  $V_{BB}$  detector of the receive dynamic limiter on pin LSAO acts continuously, discharging the capacitor connected to pin DLC. In the DC condition, the loudspeaker is then automatically disabled below this voltage.

When  $V_{BB}$  goes below 2.5 V, the TEA1098A is forced into a low voltage mode whatever the levels on the logic inputs are. It is a speech mode with reduced performances only enabling the microphone channel (between the MIC inputs and LN) and the earpiece amplifier. These two channels are able to deliver signals for line currents as small as 3 mA. The HFC input is tied to GND sinking a current typically equal to 300  $\mu$ A.

#### POWER-DOWN MODE (PIN PD)

To reduce consumption during dialling or register recall (flash), the TEA1098A is provided with a power-down input ( $\overline{PD}$ ). When the voltage on pin  $\overline{PD}$  is LOW, the current consumption from V<sub>BB</sub> and V<sub>DD</sub> is reduced to 460  $\mu$ A typically. Therefore a capacitor of 470  $\mu$ F on V<sub>BB</sub> is sufficient to power the TEA1098A during pulse dialling or flash. The  $\overline{PD}$  input has a pull-up structure. In this mode, the capacitor C<sub>REG</sub> is internally disconnected.

#### TEA1098A

# Transmit channels (pins MIC+, MIC-, DTMF, HFTX and LN)

HANDSET MICROPHONE AMPLIFIER (PINS MIC+, MIC-AND LN)

The TEA1098A has symmetrical microphone inputs. The input impedance between pins MIC+ and MIC– is typically 70 k $\Omega$ . The voltage gain between pins MIC+/MIC– and LN is set to 44.3 dB. Without limitation from the output, the microphone input stage can accommodate signals up to 18 mV (RMS) at room temperature for 2% of Total Harmonic Distortion (THD). The microphone inputs are biased at one diode voltage.

Automatic gain control is provided for line loss compensation.

DTMF AMPLIFIER (PINS DTMF, LN AND RECO)

The TEA1098A has an asymmetrical DTMF input. The input impedance between pins DTMF and GND is typically 20 k $\Omega$ . The voltage gain between pins DTMF and LN is set to 25.35 dB. Without limitation from the output, the input stage can accommodate signals up to 180 mV (RMS) at room temperature for 2% of THD.

When the DTMF amplifier is enabled, dialling tones may be sent on the line. These tones can be heard in the earpiece or in the loudspeaker at a low level. This is called the confidence tone. The voltage attenuation between pins DTMF and RECO is typically –16.5 dB in handsfree mode (HFC HIGH), and –28.2 dB in handset mode (HFC LOW).

The DC biasing of this input is 0 V.

The automatic gain control has no effect on these channels.

HANDSFREE TRANSMIT AMPLIFIER (PINS HFTX AND LN)

The TEA1098A has an asymmetrical HFTX input, which is mainly intended for use in combination with the TXO output. The input impedance between pins HFTX and GND is typically 20 k $\Omega$ . The voltage gain between pins HFTX and LN is set to 34.7 dB. Without limitation from the output, the input stage can accommodate signals up to 95 mV (RMS) at room temperature for 2% of THD. The HFTX input is biased at two diodes voltage.

Automatic gain control is provided for line loss compensation.

# Receive channels (pins IR, RECO, GARX, EARO and EVCI)

RX AMPLIFIER (PINS IR, RECO AND EVCI)

The receive amplifier has one input IR which is referred to the line. The input impedance between pins IR and LN is typically 20 k $\Omega$  and the DC biasing between these pins is equal to one diode voltage.

When HFC = 0, the gain between pins IR (referred to LN) and RECO is typically 17.2 dB which compensates typically 15 dB lower than attenuation of the anti-sidetone network. The receive amplifier gain can be digitally increased with the 4-level logic input EVCI, providing 4 steps of 4.85 dB which apply in all handset receive modes. A proportional voltage decoder at pin EVCI (see Fig.17) defines a gain of 17.2 dB when EVCI = 0 (minimum gain) and 31.7 dB (maximum gain) when EVCI = V<sub>DD</sub>; intermediate steps correspond to EVCI =  $\frac{1}{3}$ V<sub>DD</sub> and EVCI =  $\frac{2}{3}$ V<sub>DD</sub> levels. Without limitation from the output, the input stage can accommodate signals up to 50 mV (RMS) at room temperature for 2% of THD.

When HFC = 1, the gain is set automatically to 29.7 dB which compensate the anti-sidetone network attenuation minus 2.3 dB.

This receive amplifier has a rail-to-rail output RECO, which is designed for use with high ohmic (real) loads (larger than 5 k $\Omega$ ). This output is biased at two diodes voltage.

Automatic gain control is provided for line loss compensation.

EARPIECE AMPLIFIER (PINS GARX AND EARO)

The earpiece amplifier is an operational amplifier having its output (EARO) and its inverting input (GARX) available. Its input signal comes, via a decoupling capacitor, from the receive output RECO. It is used in combination with two resistors to get the required gain or attenuation compared to the receive gain. The typical resistor ratio is 4, which gives a 12 dB gain. The gain range can be chosen between 0 dB and 20 dB.

Two external capacitors  $C_{GAR}$  (connected between pins GAR and EARO) and  $C_{GARS}$  (connected between pins GAR and GND) ensure stability. The  $C_{GAR}$  capacitor provides a first-order low-pass filter. The cut-off frequency corresponds to the time constant  $C_{GAR} \times R_{E2}$ . The relationship  $C_{GARS} \geq 10 \times C_{GAR}$  must be fulfilled.

#### TEA1098A

The earpiece amplifier has a rail-to-rail output EARO, biased at two diodes voltage. It is designed for use with low ohmic (real) loads (150  $\Omega$ ) or capacitive loads (100 nF in series with 100  $\Omega$ ).

#### AGC (pin AGC)

The TEA1098A performs automatic line loss compensation, which fits well with the true line attenuation. The automatic gain control varies the gain of some transmit and receive amplifiers in accordance with the DC line current. The control range is 6.45 dB for  $G_{v(MIC-LN)}$  and  $G_{v(IR-RECO)}$  and 6.8 dB for  $G_{v(HFTX-LN)}$ , which corresponds approximately to a line length of 5.5 km for a 0.5 mm twisted-pair copper cable.

To enable this gain control, pin AGC must be shorted to pin LN. The start current for compensation corresponds to a line current of typically 23 mA and the stop current to 57 mA. The start current can be increased by connecting an external resistor between pins AGC and LN. It can be increased up to 40 mA (using a resistor typically 80 k $\Omega$ ). The start and stop current will be maintained in a ratio equal to 2.5. By leaving the AGC pin open-circuit, the gain control is disabled and no line loss compensation is performed.

#### Handsfree application

As can be seen from Fig.6, a loop is formed via the sidetone network in the line interface part and the acoustic

coupling between loudspeaker and microphone of the handsfree part.

When this loop gain is greater than 1, howling occurs. In a full duplex application this would be the case. The loop-gain has to be much lower than 1 and therefore has to be decreased to avoid howling.

This is achieved by the duplex controller. The duplex controller of the TEA1098A detects which channel has the 'largest' signal and then controls the gains of the microphone and loudspeaker amplifiers so that the sum of the gains remains constant.

As a result, in handsfree application, the circuit can be in three stable modes:

1. Transmit mode (TX mode).

The gain of the microphone amplifier is at its maximum and the gain of the loudspeaker amplifier is at its minimum.

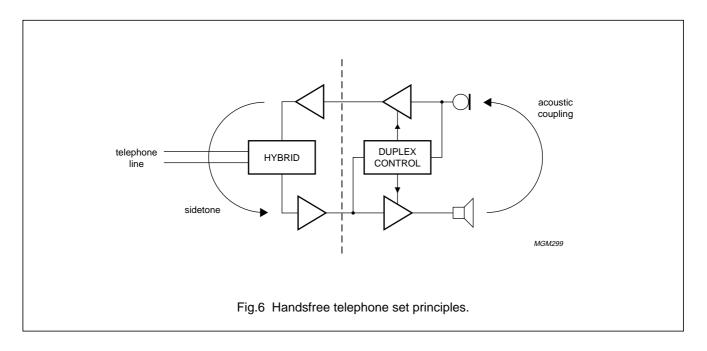
2. Receive mode (RX mode).

The gain of the loudspeaker amplifier is at its maximum and the gain of the microphone amplifier is at its minimum.

3. Idle mode.

The gain of the amplifiers is halfway between their maximum and minimum value.

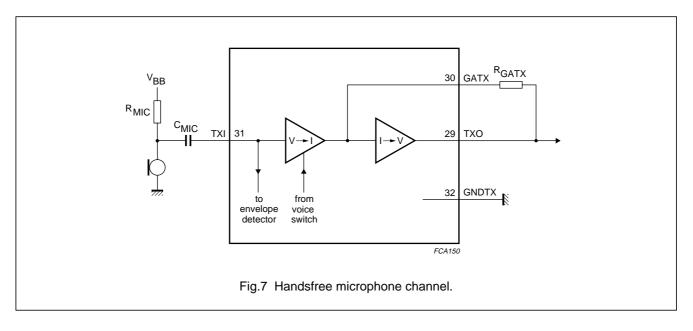
The difference between the maximum gain and minimum gain is called the switching range.



TEA1098A

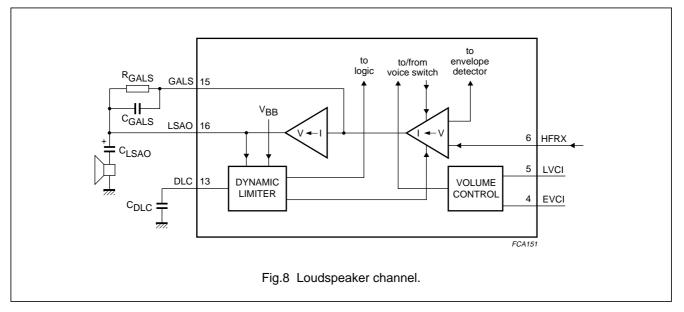
HANDSFREE MICROPHONE CHANNEL (PINS TXI, GATX, TXO AND GNDTX; SEE Fig.7)

The TEA1098A has an asymmetrical handsfree microphone input (pin TXI) with an input resistance of  $20 \text{ k}\Omega$ . The DC biasing of the input is 0 V. The gain of the input stage varies according to the mode of the TEA1098A. In the transmit mode, the gain is at its maximum; in the receive mode, it is at its minimum and in the Idle mode, it is halfway between maximum and minimum.



Switch-over from one mode to the other is smooth and click-free. The output TXO is biased at two diodes voltage and has a current capability equal to 20  $\mu$ A (RMS). In the transmit mode, the overall gain of the microphone amplifier (from pins TXI to TXO) can be adjusted from 0 dB up to 31 dB to suit specific application requirements. The gain is proportional to the value of R<sub>GATX</sub> and equals 15.2 dB with R<sub>GATX</sub> = 30.1 k $\Omega$ . Without limitation from the output, the microphone input stage can accommodate signals up to 18 mV (RMS) at room temperature for 2% of THD.

LOUDSPEAKER CHANNEL



#### TEA1098A

#### Loudspeaker amplifier (pins HFRX, GALS and LSAO)

The TEA1098A has an asymmetrical input for the loudspeaker amplifier with an input resistance of 20 k $\Omega$  between pins HFRX and GND. It is biased at two diodes voltage. Without limitation from the output, the input stage can accommodate signals up to 580 mV (RMS) at room temperature for 2% of THD.

The gain of the input stage varies according to the mode of the TEA1098A. In the receive mode, the gain is at its maximum; in the transmit mode, it is at its minimum and in the Idle mode, it is halfway between maximum and minimum. Switch-over from one mode to the other is smooth and click-free. The rail-to-rail output stage is designed to power a loudspeaker connected as a single-ended load (between pins LSAO and GND).

In the receive mode, the overall gain of the loudspeaker amplifier can be adjusted from 0 dB up to 35 dB to suit specific application requirements. The gain from HFRX to LSAO is proportional to the value of R<sub>GALS</sub> and equals 28 dB with R<sub>GALS</sub> = 255 k $\Omega$ . A capacitor connected in parallel with R<sub>GALS</sub> is recommended and provides a first-order low-pass filter.

#### Digital volume control (pins LVCI and EVCI)

The loudspeaker amplifier gain can be adjusted (attenuated) with the LVCI logic input (as MSB) and the 4-level input EVCI (as LSBs). This combination provides 8 steps of -3.85 dB which apply in all handsfree receive modes. Maximum gain (27 dB) is obtained for LVCI = V<sub>DD</sub> and EVCI = V<sub>DD</sub>; minimum gain (0 dB) is defined by LVCI = 0 and EVCI = 0. In-between steps correspond to the combination of LVCI with EVCI intermediary levels of  $\frac{1}{3}$ V<sub>DD</sub> and  $\frac{2}{3}$ V<sub>DD</sub> (see Fig.17). E.g. the first attenuation step is given by LVCI = V<sub>DD</sub> and EVCI =  $\frac{2}{3}$ V<sub>DD</sub>.

#### Dynamic limiter (pin DLC)

The dynamic limiter of the TEA1098A prevents clipping of the loudspeaker output stage and protects the operation of the circuit when the supply voltage at  $V_{BB}$  falls below 2.7 V.

Hard clipping of the loudspeaker output stage is prevented by rapidly reducing the gain when the output stage starts to saturate. The time in which gain reduction is effected (clipping attack time) is approximately a few milliseconds. The circuit stays in the reduced gain mode until the peaks of the loudspeaker signals no longer cause saturation. The gain of the loudspeaker amplifier then returns to its normal value within the clipping release time (typically 250 ms). Both attack and release times are proportional to the value of the capacitor  $C_{DLC}$ . The total harmonic distortion of the loudspeaker output stage, in reduced gain mode, stays below 2% up to 10 dB (minimum) of input voltage overdrive [providing  $V_{HFRX}$  is below 580 mV (RMS)].

When the supply voltage drops below an internal threshold voltage of 2.7 V, the gain of the loudspeaker amplifier is rapidly reduced (approximately 1 ms). When the supply voltage exceeds 2.7 V, the gain of the loudspeaker amplifier is increased again. By forcing a level lower than 0.2 V on pin DLC, the loudspeaker amplifier is muted and the TEA1098A is automatically forced into the transmit mode.

#### DUPLEX CONTROLLER

# Signal and noise envelope detectors (pins TSEN, TENV, TNOI, RSEN, RENV and RNOI)

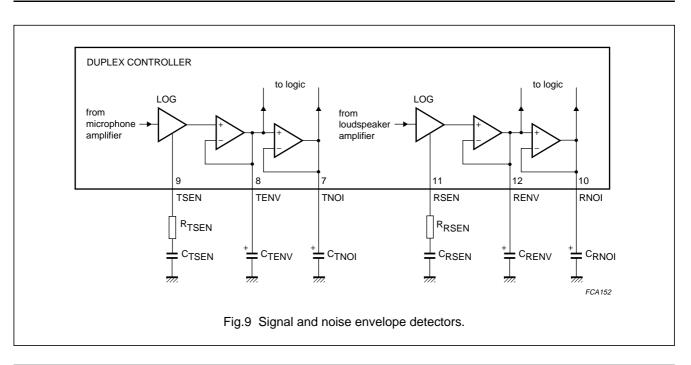
The signal envelopes are used to monitor the signal level strength in both channels. The noise envelopes are used to monitor background noise in both channels. The signal and noise envelopes provide inputs for the decision logic. The signal and noise envelope detectors are illustrated in Fig.9.

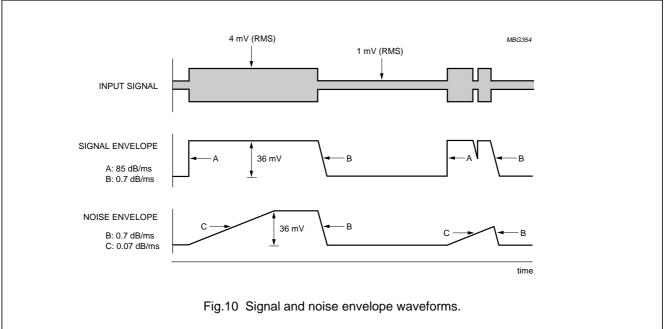
For the transmit channel, the input signal at pin TXI is 40 dB amplified to TSEN. For the receive channel, the input signal at pin HFRX is 0 dB amplified to RSEN. The signals from TSEN and RSEN are logarithmically compressed and buffered to TENV and RENV respectively.

The sensitivity of the envelope detectors is set with R<sub>TSEN</sub> and R<sub>RSEN</sub>. The capacitors connected in series with the two resistors block any DC component and form a first-order high-pass filter. In the basic application (see Fig.17) it is assumed that  $V_{TXI} = 1 \text{ mV}$  (RMS) and  $V_{HFRX} = 100 \text{ mV}$  (RMS) nominal and both R<sub>TSEN</sub> and R<sub>RSEN</sub> have a value of 10 k $\Omega$ . With the value of C<sub>TSEN</sub> and C<sub>RSEN</sub> at 100 nF, the cut-off frequency is at 160 Hz.

The buffer amplifiers feeding the compressed signals to pins TENV and RENV have a maximum source current of 120 µA and a maximum sink current of 1 µA. Capacitors CTENV and CRENV set the timing of the signal envelope monitors. In the basic application, the value of both capacitors is 470 nF. Because of the logarithmic compression, each 6 dB signal increase means 18 mV increase of the voltage on the envelopes TENV or RENV at room temperature. Thus, timings can be expressed in dB/ms. At room temperature, the 120 µA sourced current corresponds to a maximum rise-slope of the signal envelope of 85 dB/ms. This is sufficient to track normal speech signals. The 1 µA current sunk by TENV or RENV corresponds to a maximum fall-slope of 0.7 dB/ms. This is sufficient for a smooth envelope and also eliminates the effect of echoes on switching behaviour.

### TEA1098A





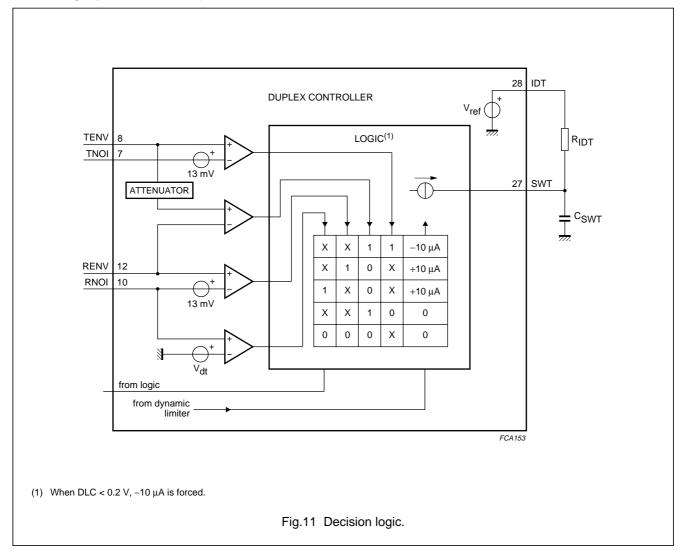
To determine the noise level, the signals on pins TENV and RENV are buffered to pins TNOI and RNOI. These buffers have a maximum source current of 1  $\mu$ A and a maximum sink current of 120  $\mu$ A. Capacitors C<sub>TNOI</sub> and C<sub>RNOI</sub> set the timing. In the basic application, see Fig.17, the value of both capacitors is 4.7  $\mu$ F. At room temperature, the 1  $\mu$ A sourced current corresponds to a maximum rise-slope of the noise envelope of approximately 0.07 dB/ms.

This is small enough to track background noise and not to be influenced by speech bursts. The 120  $\mu$ A current that is sunk corresponds to a maximum fall-slope of approximately 8.5 dB/ms. However, during the decrease of the signal envelope, the noise envelope tracks the signal envelope so it will never fall faster than approximately 0.7 dB/ms. The behaviour of the signal envelope and noise envelope monitors is illustrated in Fig.10.

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#### TEA1098A

Decision logic (pins IDT and SWT)



The TEA1098A selects its mode of operation (transmit, receive or Idle mode) by comparing the signal and the noise envelopes of both channels. This is executed by the decision logic. The resulting voltage on pin SWT is the input for the voice switch.

To facilitate the distinction between signal and noise, the signal is considered as speech when its envelope is more than 4.3 dB above the noise envelope. At room temperature, this is equal to a voltage difference  $V_{ENV} - V_{NOI} = 13 \text{ mV}$ . This so-called speech/noise threshold is implemented in both channels.

The signal on pin TXI contains both speech and the signal from the loudspeaker (acoustic coupling). When receiving, the contribution from the loudspeaker overrules the speech.

As a result, the signal envelope on pin TENV is formed mainly by the loudspeaker signal. To correct this, an attenuator is connected between pin TENV and the TENV/RENV comparator. Its attenuation equals that applied to the microphone amplifier.

When a dial tone is present on the line, without monitoring, the tone would be recognized as noise because it is a signal with a constant amplitude. This would cause the TEA1098A to go into the Idle mode and the user of the set would hear the dial tone fade away. To prevent this, a dial tone detector is incorporated which, in standard applications, does not consider input signals between HFRX and GND as noise when they have a level greater than 25 mV (RMS). This level is proportional to  $R_{RSEN}$ .

In the same way, a transmit detector is integrated which, in standard applications, does not consider input signals is at its m between pins TXI and GNDTX as noise when they have a is at its n

level greater than 0.75 mV (RMS). This level is proportional to R<sub>TSEN</sub>.

As can be seen from Fig.11, the output of the decision logic is a current source. The logic table gives the relationship between the inputs and the value of the current source. It can charge or discharge the capacitor  $C_{SWT}$  with a current of 10  $\mu$ A (switch-over). If the current is zero, the voltage on pin SWT becomes equal to the voltage on pin IDT via the high-ohmic resistor  $R_{IDT}$  (idling). The resulting voltage difference between pins SWT and IDT determines the mode of the TEA1098A and can vary between –400 and +400 mV (see Table 1).

#### Table 1 Modes of TEA1098A

V <sub>SWT</sub> – V <sub>IDT</sub> (mV)	MODE
<-180	transmit mode
0	Idle mode
>180	receive mode

The switch-over timing can be set with  $C_{SWT}$ , the Idle mode timing with  $C_{SWT}$  and  $R_{IDT}$ . In the basic application given in Fig.17,  $C_{SWT}$  is 220 nF and  $R_{IDT}$  is 2.2 M $\Omega$ . This enables a switch-over time from transmit to receive mode or vice-versa of approximately 13 ms (580 mV swing on pin SWT). The switch-over time from Idle mode to transmit mode or receive mode is approximately 4 ms (180 mV swing on pin SWT).

The switch-over time, from receive mode or transmit mode to Idle mode is equal to  $4 \times R_{IDT}C_{SWT}$  and is approximately 2 seconds (Idle mode time).

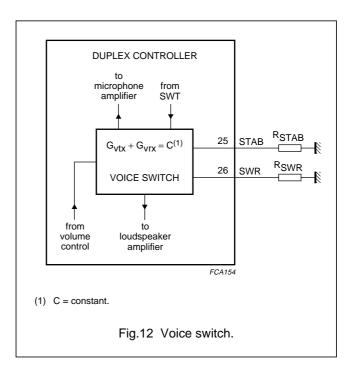
The input at pin DLC overrules the decision logic. When the voltage on pin DLC goes lower than 0.2 V, the capacitor  $C_{SWT}$  is discharged with 10  $\mu$ A thus resulting in the transmit mode.

#### Voice switch (pins STAB and SWR)

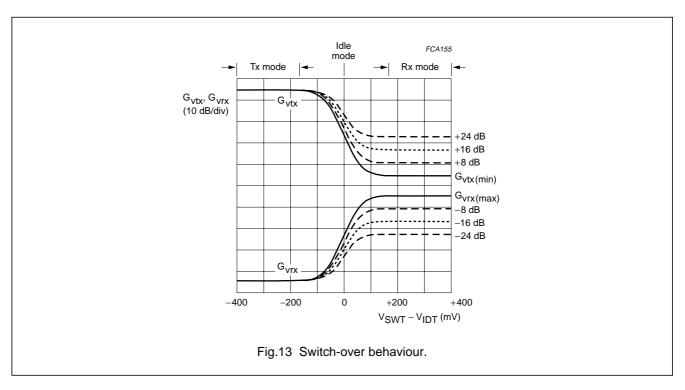
A diagram of the voice switch is illustrated in Fig.12. With the voltage on pin SWT, the TEA1098A voice switch regulates the gains of the transmit and the receive channels so that the sum of both is kept constant. In the transmit mode, the gain of the microphone amplifier is at its maximum and the gain of the loudspeaker amplifier is at its minimum. In the receive mode, the opposite applies. In the Idle mode, both microphone and loudspeaker amplifier gains are halfway.

The difference between maximum and minimum is the so called switching range. This range is determined by the ratio of R<sub>SWR</sub> and R<sub>STAB</sub> and is adjustable between 0 and 52 dB. R<sub>STAB</sub> should be 3.65 k $\Omega$  and sets an internally used reference current. In the basic application diagram given in Fig.17, R<sub>SWR</sub> is 365 k $\Omega$  which results in a switching range of 40 dB. The switch-over behaviour is illustrated in Fig.13.

In the receive mode, the gain of the loudspeaker amplifier can be reduced using the volume control. Since the voice switch keeps the sum of the gains constant, the gain of the microphone amplifier is increased at the same time (see dashed curves in Fig.13). In the transmit mode, however, the volume control has no influence on the gain of the microphone amplifier or the gain of the loudspeaker amplifier. Consequently, the switching range is reduced when the volume is reduced. At maximum reduction of volume, the switching range becomes 0 dB.



#### TEA1098A



#### Logic inputs

The actions of the logic inputs BPC and MUTE, combined with the HFC input are detailed in Table 2.

L	LOGIC INPUTS		FEATURES	
HFC	MUTE	BPC	FEATORES	APPLICATION
0	0	0	DTMF to RECO; RECO to EARO; MICS is active	handset beep mode
0	0	1	DTMF to LN; DTMF to RECO; RECO to EARO; MICS is active	handset dialling mode
0	1	0	IR to RECO; RECO to EARO; MICS is active	handset secret mode
0	1	1	MIC to LN; IR to RECO; RECO to EARO; MICS is active	handset conversation mode
1	0	0	DTMF to RECO; HFRX to LSAO; MICS is active	handsfree beep mode
1	0	1	DTMF to LN; DTMF to RECO; HFRX to LSAO; MICS is active	handsfree dialling mode
1	1	0	IR to RECO; HFRX to LSAO; MICS is active	handsfree secret mode
1	1	1	TXI to TXO; HFTX to LN; IR to RECO; HFRX to LSAO; MICS is active	handsfree conversation mode

 Table 2
 Table of switch management

#### TEA1098A

#### LIMITING VALUES

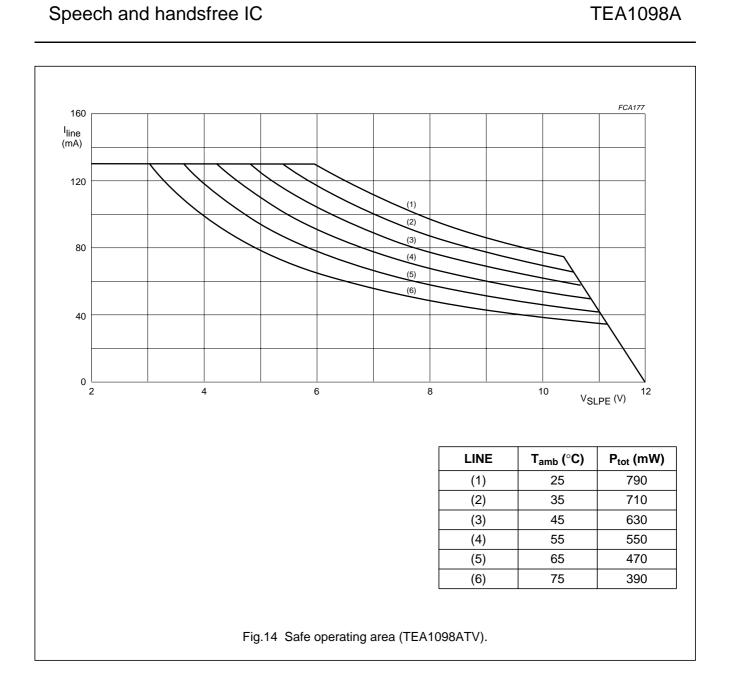
SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V <sub>LN</sub>	positive continuous line voltage		-0.4	+12	V
	repetitive line voltage during switch-on or line interruption		-0.4	+13.2	V
V <sub>n(max)</sub>	maximum voltage on pins REG, SLPE, IR and AGC		-0.4	V <sub>LN</sub> + 0.4	V
	maximum voltage on all other pins except V <sub>DD</sub>		-0.4	V <sub>BB</sub> + 0.4	V
I <sub>line</sub>	maximum line current		_	130	mA
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> = 75 °C			
	TEA1098ATV	see Fig.14	_	400	mW
	TEA1098AUH	see Fig.15	_	720	mW
T <sub>stg</sub>	storage temperature		-40	+125	°C
T <sub>amb</sub>	ambient temperature		-25	+75	°C

#### THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	in free air		
	TEA1098ATV		117	K/W
	TEA1098AUH		note 1	_

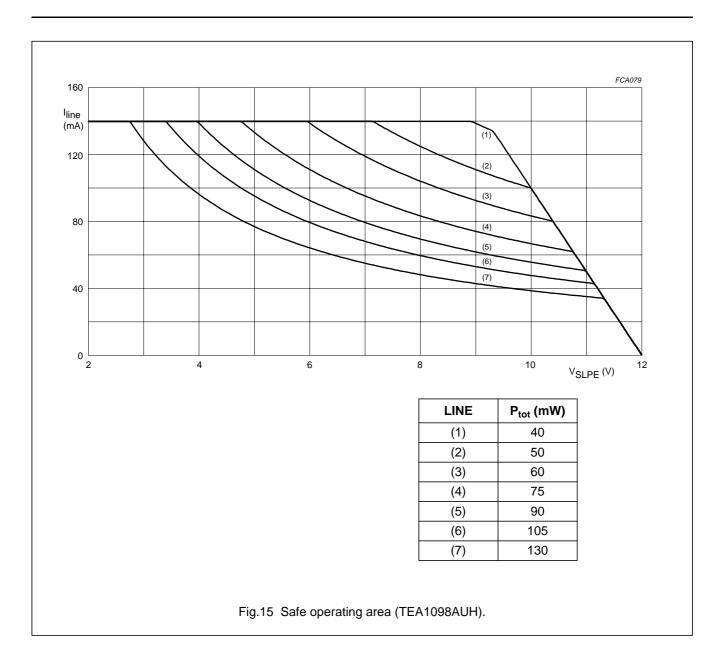
Note

1. The value is to be determined by the customer in the application.



**TEA1098A** 

# Speech and handsfree IC



#### TEA1098A

#### CHARACTERISTICS

 $I_{line} = 15 \text{ mA}; R_{SLPE} = 20 \Omega; Z_{line} = 600 \Omega; f = 1 \text{ kHz}; T_{amb} = 25 \text{ °C for TEA1098ATV}; T_j = 25 \text{ °C for TEA1098AUH}; AGC pin connected to LN; <math>\overline{PD} = HIGH; HFC = LOW; \overline{MUTE} = HIGH; \overline{BPC} = HIGH; all DC levels are referenced to GND; unless otherwise specified.}$ 

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
Supplies			1	- <b>I</b>	I	
LINE INTERFACE	AND INTERNAL SUPPLY (PINS	LN, SLPE, REG AND V <sub>BB</sub> )				
V <sub>SLPE</sub>	stabilized voltage	I <sub>line</sub> = 15 mA	3.4	3.7	4	V
	between SLPE and GND	I <sub>line</sub> = 70 mA	5.7	6.1	6.5	V
V <sub>REF</sub>	stabilized voltage with an external resistor R <sub>VA</sub> between REG and SLPE	$R_{VA} = 40 \text{ k}\Omega$	_	4.5	-	V
$\Delta V_{REF(T)}$	stabilized voltage variation with temperature referenced to 25 °C	T <sub>amb</sub> = −25 to +75 °C	_	±60	-	mV
V <sub>LN</sub>	line voltage	I <sub>line</sub> = 1 mA	-	1.55	-	V
		I <sub>line</sub> = 4 mA	-	2.35	-	V
		I <sub>line</sub> = 15 mA	3.7	4.0	4.3	V
		I <sub>line</sub> = 130 mA	-	8.7	9.3	V
V <sub>BB</sub>	regulated supply	I <sub>line</sub> = 15 mA; I <sub>BB</sub> = 0	2.75	3.0	3.25	V
	voltage for internal circuitry	$I_{\text{line}} = 70 \text{ mA}; I_{\text{BB}} = 0$	4.9	5.3	5.7	V
l <sub>line</sub>	line current for voltage	start current	-	18	-	mA
	increase	stop current	-	45	-	mA
$\Delta V_{BB(T)}$	regulated voltage variation with temperature referenced to 25 °C	T <sub>amb</sub> = −25 to +75 °C	-	±30	-	mV
I <sub>BB</sub>	current available on	in speech mode	-	11	-	mA
	pin V <sub>BB</sub>	in handsfree mode	-	9	-	mA
SUPPLY FOR PER	RIPHERALS (PIN V <sub>DD</sub> )		•	•		
V <sub>DD</sub>	supply output voltage	V <sub>BB</sub> > 3.35 V + 0.25 V (typ.)	3.1	3.35	3.6	V
		otherwise	-	V <sub>BB</sub> - 0.25	-	V
$\Delta V_{DD(T)}$	regulated voltage variation with temperature referenced to 25 °C	T <sub>amb</sub> = -25 to +75 °C; V <sub>BB</sub> > 3.35 V + 0.25 V (typ.)	-	±30	-	mV
I <sub>DD</sub>	current consumption on $V_{DD}$	in trickle mode; $I_{line} = 0$ mA; V <sub>DD</sub> = 1.5 V; V <sub>BB</sub> discharging	-	15	150	nA
I <sub>DD(ext)</sub>	current sunk from external source	in ringer mode; I <sub>line</sub> = 0; V <sub>DD</sub> = 3.35 V	-	-	75	mA

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I <sub>DD(O)</sub>	current available for peripherals	V <sub>DD</sub> = 3.3 V	-	-3	-	mA
SUPPLY FOR MIC	ROPHONE (PIN MICS)					
V <sub>MICS</sub>	supply voltage for a microphone		-	2.0	-	V
POWER-DOWN IN	IPUT (PIN PD)					•
V <sub>IL</sub>	LOW-level input voltage		-0.4	-	+0.3	V
l <sub>i(PD)(l)</sub>	input current at low voltage		-	-3	-6	μA
V <sub>IH</sub>	HIGH-level input voltage		1.4	-	V <sub>BB</sub> + 0.3	V
I <sub>BB(PD)</sub>	current consumption on $V_{BB}$ during power-down phase	PD = LOW	_	460	-	μA
Preamplifier in	puts (pins MIC+, MIC–, IR	, DTMF, TXI, HFTX and HF	FRX)	- 1	1	-
Z <sub>i(MIC)</sub>	input impedance					
	differential between pins MIC+ and MIC-		-	70	-	kΩ
	single-ended between pins MIC+/MIC- and GNDTX		-	35	_	kΩ
Z <sub>i(IR)</sub>	input impedance between pins IR and LN		-	20	-	kΩ
Z <sub>i(DTMF)</sub>	input impedance between pins DTMF and GND		_	20	-	kΩ
Z <sub>i(TXI)</sub>	input impedance between pins TXI and GNDTX		-	20	-	kΩ
Z <sub>i(HFTX)</sub>	input impedance between pins HFTX and GND		-	20	_	kΩ
Z <sub>i(HFRX)</sub>	input impedance between pins HFRX and GND		-	20	-	kΩ
TX amplifiers		·				
TX HANDSET MIC	ROPHONE AMPLIFIER (PINS N	1IC+, MIC– and LN)				
$G_{v(MIC-LN)}$	voltage gain from pin MIC+/MIC- to LN	V <sub>MIC</sub> = 5 mV (RMS)	43.3	44.3	45.3	dB
$\Delta G_{v(f)}$	gain variation with frequency referenced to 1 kHz	f = 300 to 3400 Hz	-	±0.25	-	dB
	1	1		1		

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$\Delta G_{v(T)}$	gain variation with temperature referenced to 25 °C	$T_{amb} = -25 \text{ to } +75 \text{ °C}$	-	±0.25	-	dB
CMRR	common mode rejection ratio		-	80	-	dB
THD	total harmonic	V <sub>LN</sub> = 1.4 V (RMS)	_	-	2	%
	distortion at LN	I <sub>line</sub> = 4 mA; V <sub>LN</sub> = 0.12 V (RMS)	-	-	10	%
V <sub>no(LN)</sub>	noise output voltage at pin LN; pins MIC+/MIC- shorted through 200 $\Omega$	psophometrically weighted (p53 curve)	-	-77	-	dBmp
$\Delta G_{v(mute)}$	gain reduction when muted	MUTE = 0; see Table 2	60	80	-	dB
$\Delta G_{v(MIC)(mute)}$	gain reduction in microphone mute mode	$V_{MIC} = 10 \text{ mV} (RMS);$ $\overline{MUTE} = 1; \overline{BPC} = 0;$ see Table 2	60	-	-	dB
DTMF AMPLIFIER	(PINS DTMF, LN AND REC	O)	·		·	
$G_{v(\text{DTMF-LN})}$	voltage gain from pin DTMF to LN	V <sub>DTMF</sub> = 50 mV (RMS)	24.35	25.35	26.35	dB
$\Delta G_{v(f)}$	gain variation with frequency referenced to 1 kHz	f = 300 to 3400 Hz	-	±0.25	-	dB
$\Delta G_{v(T)}$	gain variation with temperature referenced to 25 °C	$T_{amb} = -25 \text{ to } +75 \text{ °C}$	-	±0.25	-	dB
$\Delta G_{v(mute)}$	gain reduction if not active	MUTE = 1; see Table 2	60	80	-	dB
$G_{v(DTMF-RECO)}$	voltage gain from pin DTMF to RECO in handsfree mode	V <sub>DTMF</sub> = 50 mV (RMS); MUTE = 0; HFC = 1	-	-17	-	dB
$G_{v(DTMF-RECO)}$	voltage gain from pin DTMF to RECO in handset mode	V <sub>DTMF</sub> = 50 mV (RMS); MUTE = 0; HFC = 0; EVCI = 0	-	-28.2	-	dB
$\Delta G_{v(DTMF\text{-}RECO)}$	digital volume control adjustment range in handset mode	$\frac{V_{\text{DTMF}}}{\text{MUTE}} = 50 \text{ mV (RMS)};$ $\overline{\text{MUTE}} = 0; \text{HFC} = 0$	-	-12.75	-	dB
$\Delta G_{v(\text{DTMF-RECO})}$	digital volume control adjustment step in handset mode	MUTE = 0; HFC = 0; per step	-	4.25	-	dB

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
TX AMPLIFIER US	ING HFTX (PINS HFTX AND	LN)	•	- <b>I</b>		
$G_{v(\text{HFTX-LN})}$	voltage gain from pin HFTX to LN	V <sub>HFTX</sub> = 15 mV (RMS)	33.5	34.7	35.9	dB
$\Delta G_{v(f)}$	gain variation with frequency referenced to 1 kHz	f = 300 to 3400 Hz	-	±0.25	-	dB
$\Delta G_{v(T)}$	gain variation with temperature referenced to 25 °C	$T_{amb} = -25 \text{ to } +75^{\circ}\text{C}$	-	±0.35	-	dB
THD	total harmonic distortion at LN	V <sub>LN</sub> = 1.4 V (RMS)	-	-	2	%
V <sub>HFTX(rms)</sub>	maximum input voltage at HFTX (RMS value)	I <sub>line</sub> = 70 mA; THD = 2%	-	85	-	mV
V <sub>no(LN)</sub>	noise output voltage at pin LN; pin HFTX shorted to GND through 200 $\Omega$ in series with 10 $\mu$ F	psophometrically weighted (p53 curve)	-	-77	-	dBmp
$\Delta G_{v(m)}$	gain reduction when muted	MUTE = 0; see Table 2	60	80	-	dB
$\Delta G_{v(MIC)(mute)}$	gain reduction in microphone mute mode	$\overline{\text{MUTE}} = 1; \overline{\text{BPC}} = 0;$ see Table 2	60	-	_	dB
RX amplifiers			·			·
RX AMPLIFIERS U	ISING IR (PINS IR AND RECO	D)				
$G_{v(\text{IR-RECO})(\text{HF})}$	voltage gain from IR to RECO (handsfree mode)	V <sub>IR</sub> = 4 mV (RMS); HFC = 1	28.4	29.4	30.4	dB
G <sub>v(IR-RECO)(HS)</sub>	voltage gain from IR to RECO (handset mode)	V <sub>IR</sub> = 4 mV (RMS); HFC = 0; EVCI = 0	16.2	17.2	18.2	dB
$\Delta G_{v(IR-RECO)}$	digital volume control adjustment range in handset mode	$V_{IR} = 4 \text{ mV} (RMS); HFC = 0;$ EVCI = $V_{DD}$	13	14.5	16	dB
$\Delta G_{v(IR-RECO)}$	digital volume control adjustment step in handset mode	HFC = 0; per step	-	+4.85	-	dB
$\Delta G_{v(f)}$	gain variation with frequency referred to 1 kHz	f = 300 to 3400 Hz	-	±0.25	_	dB
$\Delta G_{v(T)}$	gain variation with temperature referenced to 25 °C	$T_{amb} = -25 \text{ to } +75 ^{\circ}\text{C}$	-	±0.3	-	dB
V <sub>IR(max)</sub> (rms)	maximum input voltage on IR (referenced to LN) (RMS value)	I <sub>line</sub> = 70 mA; THD = 2%	_	50	-	mV

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V <sub>RECO(max)(rms)</sub>	maximum output voltage on RECO (RMS value)	THD = 2%; $G_{v(RECO-EARO)} = 12 \text{ dB}$	0.75	0.9	-	V
V <sub>no(RECO)</sub> (rms)	noise output voltage at pin RECO; pin IR is an open-circuit (RMS value)	psophometrically weighted (p53 curve)	_	-84	-	dBVp
$\Delta G_{v(mute)}$	gain reduction if not active	MUTE = 0; see Table 2	60	80	-	dB
RX EARPIECE AME	PLIFIER (PINS GARX AND EA	ARO)				
$\Delta G_{v(RECO-EARO)}$	gain voltage range between pins RECO and EARO		0	-	20	dB
V <sub>EARO(max)</sub> (rms)	maximum output voltage on EARO (RMS value)	sine wave drive; $R_L = 150 \Omega$ ; THD < 2%	0.75	0.9	-	V
V <sub>no(EARO)</sub> (rms)	noise output voltage at pin EARO; pin IR is an open-circuit (RMS value)	$G_{v(EARO)} = 12 \text{ dB}; \text{ EVCI} = 0;$ psophometrically weighted (p53 curve)	_	-84	-	dBVp
Automatic Gain	Control (pin AGC)		•	1	ł	
$\Delta G_{v(trx)}$ gain control range for transmit and receive		$\label{eq:line} \begin{split} I_{\text{line}} &= 70 \text{ mA; } G_{v(\text{MIC}-\text{LN})}; \\ G_{v(\text{IR-RECO})};  R_{\text{AGC}} &= 0; \end{split}$	5.45	6.45	7.45	dB
	signals affected by the AGC; with respect to I <sub>line</sub> = 15 mA	$I_{line} = 70 \text{ mA for } G_{v(HFTX-LN)};$ $R_{AGC} = 0$	5.8	6.8	7.8	dB
I <sub>start</sub>	highest line current for maximum gain		-	23	-	mA
I <sub>stop</sub>	lowest line current for maximum gain		-	57	-	mA
$\Delta I_{\text{start}}$	$I_{start}$ adjustment range with $R_{AGC}$		-	-	40	mA
Logic inputs (pi	ns HFC, $\overline{\text{MUTE}}$ , and $\overline{\text{BPC}}$	)				
V <sub>IL</sub>	LOW-level input voltage		-0.4	_	+0.3	V
V <sub>IH</sub>	HIGH-level input voltage		1.4	-	V <sub>BB</sub> + 0.3	V
I <sub>i(I)</sub>	input current at low voltage	V <sub>BB</sub> = 3.0 V				
	for pin HFC for pin MUTE		-  -	0 -5	-	μΑ μΑ
	for pin BPC		-	-2.5	-	μA

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
l <sub>i(h)</sub>	input current at high voltage	V <sub>BB</sub> = 3.0 V				
	for pin HFC		-	2.5	-	μA
	for pin MUTE		-	0	-	μA
	for pin BPC		-	0	-	μA
Handsfree mod	le (HFC = HIGH)					
HF MICROPHONE	AMPLIFIER (PINS TXI, TXO	AND GATX)				
G <sub>v(TXI-TXO)</sub>	voltage gain from pin TXI to TXO		12.7	15.2	17.7	dB
$\Delta G_v$	voltage gain adjustment with $R_{\text{GATX}}$		-15	-	+16	dB
$\Delta G_{v(f)}$	gain variation with frequency referenced to 1 kHz	f = 300 to 3400 Hz	_	±0.1	_	dB
$\Delta G_{v(T)}$	gain variation with temperature referenced to 25 °C	T <sub>amb</sub> = −25 to +75 °C	-	±0.15	-	dB
V <sub>no(TXO)(rms)</sub>	$\begin{array}{c} \mbox{noise output voltage at} \\ \mbox{pin TXO; pin TXI is} \\ \mbox{shorted through 200 } \Omega \\ \mbox{and 10 } \mu \mbox{F to GNDTX} \end{array}$	psophometrically weighted (p53 curve); G <sub>v(TXI)</sub> = 15 dB; RMS value	-	-101	-	dBVp
$\Delta G_{v(mute)}$	gain reduction when muted	MUTE = 0; see Table 2	60	80	-	dB
$\Delta G_{v(SEC)}$	gain reduction in secret mode	$\label{eq:txi} \begin{array}{l} V_{txi} = 10 \text{ mV} (\text{RMS});\\ \hline \text{MUTE} = 1; \text{ BPC} = 0;\\ \text{see Table 2} \end{array}$	60	_	_	dB
HF LOUDSPEAKE	R AMPLIFIER (PINS HFRX, LS	SAO, GALS AND DLC)	•			•
$G_{v(HFRX-LSAO)}$	nominal voltage gain from pin HFRX to LSAO		24.5	27	29.5	dB
$\Delta G_{v(HFRX-LSAO)}$	digital volume control adjustment range	$V_{HFRX}$ = 30 mV (RMS); R <sub>GALS</sub> = 255 k $\Omega$	25.5	27	28.5	dB
$\Delta G_{v(step)}$	digital volume adjustment step	per step	-	3.85	-	dB
$\Delta G_v$	voltage gain adjustment with $R_{GALS}$		-28	-	+7	dB
$\Delta G_{v(f)}$	gain variation with frequency referenced to 1 kHz	f = 300 to 3400 Hz	-	±0.3	_	dB
$\Delta G_{v(T)}$	gain variation with temperature referenced to 25 °C	T <sub>amb</sub> = −25 to +75 °C	-	±0.3	-	dB
V <sub>HFRX(max)(rms)</sub>	maximum input voltage at pin HFRX (RMS value)	$I_{\text{line}} = 70 \text{ mA};$ $R_{\text{GALS}} = 33 \text{ k}\Omega;$ for 2% THD in the input stage	-	580	-	mV

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V <sub>no(LSAO)</sub> (rms)	noise output voltage at pin LSAO; pin HFRX is open-circuit (RMS value)	psophometrically weighted (p53 curve); LVCI = $V_{DD}$ ; EVCI = $V_{DD}$	-	-79	-	dBVp
$\Delta G_{v(mute)}$	gain reduction if not active	see Table 2	60	-	-	dB
VLSAO(rms)	output voltage capability (RMS value) at pin LSAO with sine wave signal and loaded with 50 $\Omega$ + 220 $\mu$ F; G <sub>vLSAO</sub> = 28 dB	$I_{BB} = 1 \text{ mA}; I_{DD} = 1 \text{ mA}$ $I_{line} = 18 \text{ mA}$ $I_{line} = 30 \text{ mA}$ $I_{line} > 50 \text{ mA}$	- - -	- 0.9 1.3 1.6		V V V
I <sub>LSAO(max)</sub>	maximum output current at pin LSAO (peak value)		150	300	-	mA
DYNAMIC LIMITER	R (PINS LSAO AND DLC)			·	·	
t <sub>att</sub>	attack time	when V <sub>HFRX</sub> jumps up from 20 mV to 20 mV +10 dB	-	-	5	ms
		when $V_{BB}$ drops below $V_{BB(th)}$	-	1	-	ms
t <sub>rel</sub>	release time	when V <sub>HFRX</sub> jumps down from 20 mV +10 dB to 20 mV	_	100	-	ms
THD	total harmonic distortion	$\label{eq:VHFRX} \begin{array}{l} V_{HFRX} = 20 \mbox{ mV} + 10 \mbox{ dB}; \\ G_{v(LSAO)} = 28 \mbox{ dB}; \mbox{ t} > t_{att} \end{array}$	-	1	2	%
V <sub>BB(th)</sub>	V <sub>BB</sub> limiter threshold		-	2.7	-	V
MUTE RECEIVE (	PIN DLC)					
V <sub>DLC(th)</sub>	threshold voltage required on pin DLC to obtain mute receive condition		-	_	0.2	V
I <sub>DLC(th)</sub>	Start-up current sourced by pin DLC	$V_{DLC} = 0.2 V$	-	100	-	μA
$\Delta G_{vrx(m)}$	voltage gain reduction in mute receive condition	V <sub>DLC</sub> = 0.2 V	60	80	-	dB
TX AND RX ENV	ELOPE AND NOISE DETECTOR	S (PINS TSEN, TENV, TNOI, R	SEN, REN	IV AND RNO	9I)	
Preamplifiers						
G <sub>v(TSEN)</sub>	voltage gain from pin TXI to TSEN		-	40	-	dB
G <sub>v(RSEN)</sub>	voltage gain from pin HFRX to RSEN		_	0	-	dB

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
Logarithmic con	mpressor and sensitivity adj	ustment	<b>!</b>			
$\Delta V_{det(TSEN)}$	sensitivity detection on pin TSEN; voltage change on pin TENV when doubling the current from TSEN	I <sub>TSEN</sub> = 0.8 to 160 μA	-	18	_	mV
$\Delta V_{det(RSEN)}$	sensitivity detection on pin RSEN; voltage change on pin RENV when doubling the current from RSEN	I <sub>RSEN</sub> = 0.8 to 160 μA	_	18	-	mV
Signal envelope	e detectors					
I <sub>source</sub> (ENV)	maximum current sourced from pin TENV or RENV		-	120	-	μA
l <sub>sink(ENV)</sub>	maximum current sunk by pin TENV or RENV		-1.25	-1	-0.75	μA
$\Delta V_{\sf ENV}$	voltage difference between RENV and TENV	10 μA sourced from both RSEN and TSEN; signal detectors tracking; note 1	-	±3	-	mV
Noise envelope	detectors					
I <sub>source(NOI)</sub>	maximum current sourced from pin TNOI or RNOI		0.75	1	1.25	μA
I <sub>sink(NOI)</sub>	maximum current sunk by pin TNOI or RNOI		-	-120	-	μA
$\Delta V_{NOI}$	voltage difference between pins RNOI and TNOI	5 μA sourced from both RSEN and TSEN; noise detectors tracking; note 1	-	±3	-	mV
DIAL TONE DETER	CTOR		ł	·		
V <sub>HFRX(th)(rms)</sub>	threshold level at pin HFRX (RMS value)	$R_{RSEN} = 10 \text{ k}\Omega;$ $C_{RSEN} = 100 \text{ nF}$	-	25	_	mV
TX LEVEL LIMITE	R					
V <sub>TXI(th)</sub> (rms)	threshold level at pin TXI (RMS value)	R <sub>TSEN</sub> = 10 kΩ	-	0.75	_	mV
DECISION LOGIC	(PINS IDT AND SWT)					
Signal recogniti	on					
$\Delta V_{Strx(th)}$	threshold voltage between RENV/RNOI or between TENV/TNOI to switch-over from Idle mode to RX/TX mode	V <sub>HFRX</sub> < V <sub>HFRX(th)</sub> ; V <sub>TXI</sub> < V <sub>TXI(th)</sub> ; note 2	-	13	_	mV

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SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
Switch-over		1			<b>I</b>	
I <sub>source(SWT)</sub>	current sourced from pin SWT when switching to receive mode		7.5	10	12.5	μA
I <sub>sink(SWT)</sub>	current sunk by pin SWT when switching to transmit mode		-12.5	-10	-7.5	μA
I <sub>idle(SWT)</sub>	current sourced from pin SWT in Idle mode		_	0	-	μA
VOICE SWITCH (F	PINS STAB AND SWR)			•		
SWR	switching range		_	40	_	dB
ΔSWR	switching range adjustment	with $R_{SWR}$ referenced to 365 k $\Omega$	-40	-	+12	dB
$ \Delta G_v $	voltage gain variation from active modes to Idle mode	SWRA = 40 dB	-	±20	-	dB
G <sub>tr</sub>	gain tracking (G <sub>vtx</sub> + G <sub>vrx</sub> ) during switching, referred to Idle mode		_	±0.5	-	dB

#### Notes

1. Corresponds to  $\pm 1$  dB tracking.

2. Corresponds to 4.3 dB noise/speech recognition level.

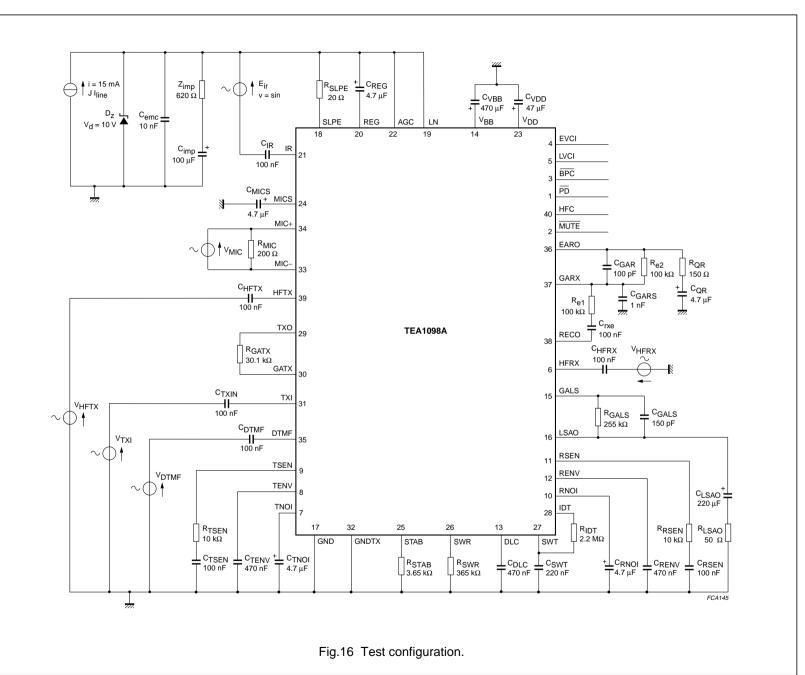


# Product specification

# Speech and handsfree IC

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R<sub>VCIL</sub> C<sub>bal</sub> R<sub>bal2</sub> LV0 820 Ω 220 nF 360 kΩ  $\begin{array}{c} R_{\text{SLPE}} \\ 20 \ \Omega \end{array} \stackrel{\text{+}}{-} \begin{array}{c} C_{\text{REG}} \\ \text{-} 4.7 \ \mu\text{F} \end{array}$ RVCIH R<sub>bal1</sub> Z<sub>imp</sub> 620 Ω CVBB CVDD - LV1 130 Ω 180 kΩ R<sub>ast3</sub> ± 47 μF . D<sub>Z</sub> ÷ 470 μF Cemc 10 nF 📥 D2 👗 D3 ਙ LV2 V<sub>d</sub> = 392 Ω from  $V_{BB}$ VDD SLPE REG AGC LN EVCI LVCI + Cimp 22 μF R<sub>ast2</sub> 10 V microcontroller CIR 3.92 kΩ 18 20 22 19 14 23 4 5 BPC IR BPC ╢ 21 PD 100 nF PD Rast1 HFC 130 kΩ 40 HFC MICS MUTE CQR 7 MICS · 24 2 MUTE + C<sub>MICS</sub> 4.7 μF 10 μF EARO RMICP Ήŀ 36  $1 k\Omega C_{tx2} R_{tx2}$ MIC+ R<sub>e2</sub> ╢⊢ \_\_\_\_ 34 15 kΩ 100 pF 100 kΩ 22 nF R<sub>tx3</sub> 8.2 kΩ <u>MIC-</u> GARX handset CMICH ₩. Α-37 micro C<sub>tx1</sub> 33 nF R<sub>tx1</sub> R<sub>e1</sub> CGARS -11-33 22 nF 15 kΩ 100 kΩ C<sub>HFTX</sub> В· R<sub>MICM</sub> Crxe 777 HFTX ╢ 39 1 kΩ RECO 100 nF **TEA1098A** 100 nF 38 тхо 777. 29 CHFRX from MICS HFRX T 100 nF RGATX 6 30.1 kΩ GATX GALS RBMICS 30 15 \_ 2 kΩ C<sub>TXIN</sub> RGALS CGALS 255 kΩ 150 pF TXI C<sub>LSAO</sub> ⊣⊢ 31 220 µF 100 nF handsfree / C<sub>DTMF</sub> ⁺⊪ 16 micro DTMF 33 nF -++35 RSEN 11 100 nF Ţ, 7/7. TSEN RENV 12 TENV RNOI 10 TNOI IDT 28 🛣 D1 **D**4 RTSEN 17 32 26 27 RIDT 25 13 RRSEN 10 kΩ GND 2.2 MΩ GNDTX STAB SWR DLC SWT 10 kΩ  $\begin{array}{c} \perp C_{\text{TSEN}} \\ - 100 \text{ nF} \end{array} \begin{array}{c} \perp C_{\text{TENV}} \\ + 470 \text{ nF} \end{array} \begin{array}{c} + \perp C_{\text{TNOI}} \\ - 4.7 \mu\text{F} \end{array}$  $\frac{+ \Box C_{RNOI} \Box C_{RENV} \Box C_{RSEN}}{+ 4.7 \, \mu F} \pm 470 \, nF \pm 100 \, nF}$ R<sub>STAB</sub> 3.65 kΩ R<sub>SWR</sub> 365 kΩ ↓ C<sub>DLC</sub> 470 nF CSWT 220 nF <del>///</del>. FCA146 Fig.17 Basic application diagram.

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Speech and handsfree

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Product specification

**TEA1098A** 

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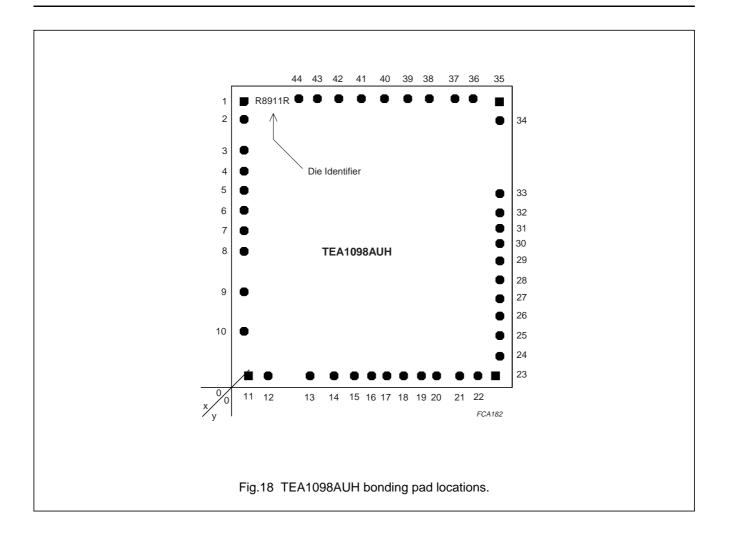
#### BONDING PAD LOCATIONS FOR TEA1098AUH

SYMBOL	BAD	COORDINATES		
STWBUL	PAD	x	у	
HFRX	1	137.5	3139.2	
TNOI	2	137.5	2944	
TENV	3	137.5	2605.8	
TSEN	4	137.5	2375.5	
TNOI	5	137.5	2164.5	
RSEN	6	137.5	1945.2	
RENV	7	137.5	1721.8	
DLC	8	137.5	1494.5	
V <sub>BB</sub>	9	137.5	1050.2	
GALS	10	137.5	616.8	
LSAO	11	185.2	128	
n.c.	12	401.2	128	
GND	13	861.5	128	
SLPE	14	1125	128	
SLPE	15	1348.2	128	
LN	16	1537.5	128	
REG	17	1704.8	128	
IR	18	1888.8	128	
AGC	19	2084	128	
V <sub>DD</sub>	20	2251	128.2	
MICS	21	2503.8	127	
STAB	22	2703.8	128.5	
SWR	23	2897	128	
n.c.	24	2944.8	343	

	DAD	COORD	DINATES
SYMBOL	PAD	x	У
SWT	25	2944.8	570
IDT	26	2945	784
ТХО	27	2945	973.8
GATX	28	2945	1182
ТХІ	29	2945	1390
GNDTX	30	2945	1581
GNDTX	31	2945	1747.8
MIC-	32	2945	1917.2
MIC+	33	2945	2129
DTMF	34	2945	2931
EARO	35	2940	3136.8
GARX	36	2651	3171.2
RECO	37	2451.8	3171.2
HFTX	38	2170.8	3171.2
HFC	39	1934.2	3171.2
PD	40	1678.8	3171.2
MUTE	41	1425	3171.2
BPC	42	1177	3171.2
EVCI	43	942.2	3171.2
LVCI	44	738.5	3171.2

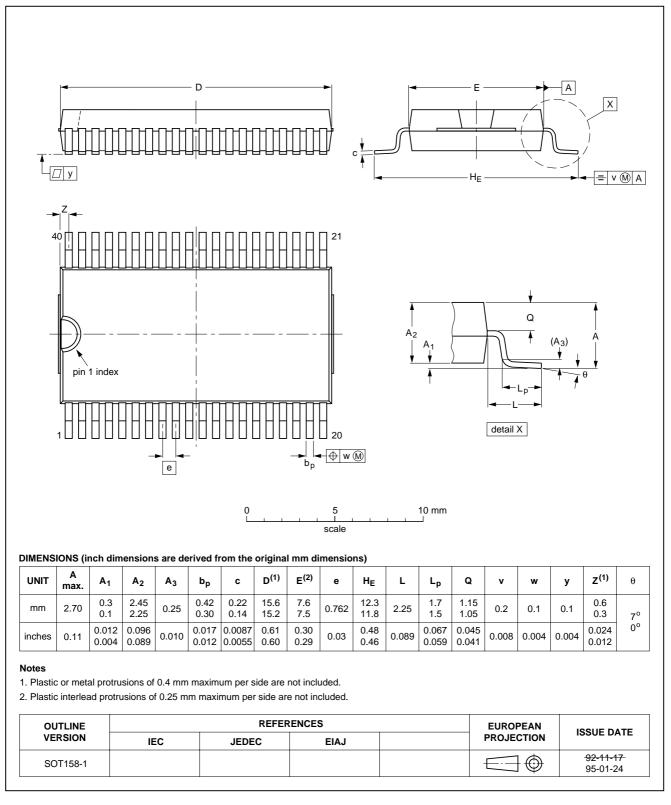
All x/y coordinates represent the position of the centre of the pad (in  $\mu$ m) with respect to the origin (x/y = 0/0) of the die (see Fig.18). The size of all pads is 80  $\mu$ m<sup>2</sup>.

# speech and hands



#### PACKAGE OUTLINE

#### VSO40: plastic very small outline package; 40 leads



## TEA1098A

#### SOLDERING

#### Introduction to soldering surface mount packages

This text gives a very brief insight to a complex technology. A more in-depth account of soldering ICs can be found in our *"Data Handbook IC26; Integrated Circuit Packages"* (document order number 9398 652 90011).

There is no soldering method that is ideal for all surface mount IC packages. Wave soldering is not always suitable for surface mount ICs, or for printed-circuit boards with high population densities. In these situations reflow soldering is often used.

#### **Reflow soldering**

Reflow soldering requires solder paste (a suspension of fine solder particles, flux and binding agent) to be applied to the printed-circuit board by screen printing, stencilling or pressure-syringe dispensing before package placement.

Several methods exist for reflowing; for example, infrared/convection heating in a conveyor type oven. Throughput times (preheating, soldering and cooling) vary between 100 and 200 seconds depending on heating method.

Typical reflow peak temperatures range from 215 to 250 °C. The top-surface temperature of the packages should preferable be kept below 230 °C.

#### Wave soldering

Conventional single wave soldering is not recommended for surface mount devices (SMDs) or printed-circuit boards with a high component density, as solder bridging and non-wetting can present major problems.

To overcome these problems the double-wave soldering method was specifically developed.

If wave soldering is used the following conditions must be observed for optimal results:

- Use a double-wave soldering method comprising a turbulent wave with high upward pressure followed by a smooth laminar wave.
- For packages with leads on two sides and a pitch (e):
  - larger than or equal to 1.27 mm, the footprint longitudinal axis is preferred to be parallel to the transport direction of the printed-circuit board;
  - smaller than 1.27 mm, the footprint longitudinal axis must be parallel to the transport direction of the printed-circuit board.

The footprint must incorporate solder thieves at the downstream end.

• For packages with leads on four sides, the footprint must be placed at a 45° angle to the transport direction of the printed-circuit board. The footprint must incorporate solder thieves downstream and at the side corners.

During placement and before soldering, the package must be fixed with a droplet of adhesive. The adhesive can be applied by screen printing, pin transfer or syringe dispensing. The package can be soldered after the adhesive is cured.

Typical dwell time is 4 seconds at 250 °C. A mildly-activated flux will eliminate the need for removal of corrosive residues in most applications.

#### Manual soldering

Fix the component by first soldering two diagonally-opposite end leads. Use a low voltage (24 V or less) soldering iron applied to the flat part of the lead. Contact time must be limited to 10 seconds at up to 300 °C.

When using a dedicated tool, all other leads can be soldered in one operation within 2 to 5 seconds between 270 and 320  $^\circ\text{C}.$ 

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#### Suitability of surface mount IC packages for wave and reflow soldering methods

PACKAGE	SOLDERING METHOD		
FACKAGE	WAVE	REFLOW <sup>(1)</sup>	
BGA, LFBGA, SQFP, TFBGA	not suitable	suitable	
HBCC, HLQFP, HSQFP, HSOP, HTQFP, HTSSOP, SMS	not suitable <sup>(2)</sup>	suitable	
PLCC <sup>(3)</sup> , SO, SOJ	suitable	suitable	
LQFP, QFP, TQFP	not recommended <sup>(3)(4)</sup>	suitable	
SSOP, TSSOP, VSO	not recommended <sup>(5)</sup>	suitable	

#### Notes

- 1. All surface mount (SMD) packages are moisture sensitive. Depending upon the moisture content, the maximum temperature (with respect to time) and body size of the package, there is a risk that internal or external package cracks may occur due to vaporization of the moisture in them (the so called popcorn effect). For details, refer to the Drypack information in the "Data Handbook IC26; Integrated Circuit Packages; Section: Packing Methods".
- 2. These packages are not suitable for wave soldering as a solder joint between the printed-circuit board and heatsink (at bottom version) can not be achieved, and as solder may stick to the heatsink (on top version).
- 3. If wave soldering is considered, then the package must be placed at a 45° angle to the solder wave direction. The package footprint must incorporate solder thieves downstream and at the side corners.
- 4. Wave soldering is only suitable for LQFP, TQFP and QFP packages with a pitch (e) equal to or larger than 0.8 mm; it is definitely not suitable for packages with a pitch (e) equal to or smaller than 0.65 mm.
- 5. Wave soldering is only suitable for SSOP and TSSOP packages with a pitch (e) equal to or larger than 0.65 mm; it is definitely not suitable for packages with a pitch (e) equal to or smaller than 0.5 mm.

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#### DATA SHEET STATUS

DATA SHEET STATUS	PRODUCT STATUS	DEFINITIONS <sup>(1)</sup>
Objective specification	Development	This data sheet contains the design target or goal specifications for product development. Specification may change in any manner without notice.
Preliminary specification	Qualification	This data sheet contains preliminary data, and supplementary data will be published at a later date. Philips Semiconductors reserves the right to make changes at any time without notice in order to improve design and supply the best possible product.
Product specification	Production	This data sheet contains final specifications. Philips Semiconductors reserves the right to make changes at any time without notice in order to improve design and supply the best possible product.

#### Note

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